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MAR 03 2005

## TRANSMITTAL OF FORMAL DRAWINGS

Docket No.

YOR920030203US1 (16694)

Re Application Of:

Stephen W. Bedell, et al.

Application No.	Filing Date	Confirmation No.	Examiner	Customer No.	Group Art Unit
10/662,028	September 12, 2003	9297	Unassigned	23389	3661

Invention: FORMATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER

Address to:

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Transmitted herewith are:

7 sheets of formal drawing(s) for this application.

- Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).

Signature

Dated: March 1, 2005

Leslie S. Szivos, Ph.D.  
Registration No. 39,394

I certify that this document and attached formal drawings are being deposited on 03/01/05 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Signature of Person Mailing Correspondence

Leslie S. Szivos, Ph.D.

Typed or Printed Name of Person Mailing Correspondence